

Innovating Energy Technology

http://www.fujielectric.com/products/semiconductor/ **FUJI POWER MOSFET**

Super J MOS[®] S2 series

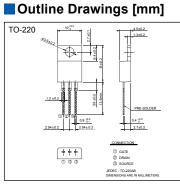
N-Channel enhancement mode power MOSFET

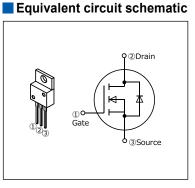
Features

Pb-free lead terminal **RoHS** compliant uses Halogen-free molding compound

Applications

For switching





Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)

Parameter	Symbol	Characteristics	Unit	Remarks
Duain Course Valtana	VDS	600	V	
Drain-Source Voltage	VDSX	600	V	V _{GS} =-30V
Continuous Drain Current	,	42.3	А	Tc=25°C Note*1,2
Continuous Drain Current	I _D	26.8	А	Tc=100°C Note*1,2
Pulsed Drain Current	I DP	131	А	Note *2
Gate-Source Voltage	V _{GS}	±30	V	
Non-Repetitive Maximum Avalanche Current	las	4.9	А	Note *3
Non-Repetitive Maximum Avalanche Energy	Eas	1018	mJ	Note *4
Maximum Drain-Source dV/dt	dV₀s/dt	50	V/ns	V _{DS} ≤ 600V
Continuous	,	42.3	А	Tc=25°C Note*1,2
Diode Forward Current	Isd	26.8	А	Tc=100°C Note*1,2
Pulsed Diode Forward Current	Isdp	131	А	Note *2
Peak Diode Recovery dV/dt	dV/dt	15	V/ns	Note *5
Peak Diode Recovery -di/dt	-di/dt	100	A/µs	Note *6
Maximum Dawar Disaination	PD	2.02	W	<i>T</i> ₂=25°C
Maximum Power Dissipation	F D	235	VV	<i>T</i> c=25°C
Operating and Storage Temperature range	Tch	150	°C	
Operating and Storage Temperature range	7 stg	-55 to +150	°C	

Note *1 : Maximum duty cycle D=0.60

Note *1 : Imited by maximum channel temperature. Note *3 : T_{ch}≤150°C, See Fig.1 and Fig.2 Note *4 : Starting T_{ch}=25°C, I_As=3A, L=207mH, V_{DD}=60V, R_G=50Ω, See Fig.1 and Fig.2 E_{AS} limited by maximum channel temperature and avalanche current. Note *5 : I_{SD}≤32.8A, -di/dt≤100A/µs, V_{DS peak}≤ 600V, T_{ch}≤150°C. Note *6 : I_{SD}≤32.8A, dV/dt≤15V/ns, V_{DS peak}≤ 600V, T_{ch}≤150°C.

Electrical Characteristics at Tc=25°C (unless otherwise specified) Static Ratings

Parameter	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I₀=250µA		600	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I₀=1.72mA		3.5	4.0	4.5	V
Zero Gate Voltage Drain Current	loss	V _{DS} =600V V _{GS} =0V	T _{ch} =25°C	-	-	25	μA
		V _{DS} =480V V _{GS} =0V	<i>T</i> _{ch} =125°C	-	-	250	
Gate-Source Leakage Current	Igss	V _{DS} =0V V _{GS} =±30V		-	10	100	nA
Drain-Source On-State Resistance	RDS(on)	V _{GS} =10V I₀=16.4A		-	0.083	0.088	Ω
Gate resistance	RG	f=1MHz, open drain		-	7.5	-	Ω

Dynamic Ratings

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	g _{fs}	V _{DS} =25V I _D =16.4A	10	20	-	S
Input Capacitance	Ciss	V _{DS} =400V	-	1830	-	
Output Capacitance	Coss	V _{GS} =0V	-	59	-	
Reverse Transfer Capacitance	Crss	f=250kHz	-	7.5	-	
Effective output capacitance, energy related (Note *7)	C _{o(er)}	V _{DS} =0400V V _{GS} =0V	-	138	-	pF
Effective output capacitance, time related (Note *8)	Co(tr)	V₀s=0400V V₀s=0V I₀=constant	-	546	-	
	t _{d(on)}	V_DD=400V. V_GS=10V	-	31	-	- ns
Turn-On Time	tr	$I_{D} = 16.4A,$	-	92	-	
	t _{d(off)}	R _s =15Ω See Fig.3 and Fig.4	-	129	-	
Turn-Off Time	<i>t</i> r		-	24	-	
Total Gate Charge	QG		-	72	-	nC
Gate-Source Charge	Q _{GS}	V_{DD} =400V, V_{GS} =10V	-	30	-	
Gate-Drain Charge	QGD	_ /₀=32.8A See Fig.5	-	29	-	
Drain-Source crossover Charge	Qsw		-	21	-	

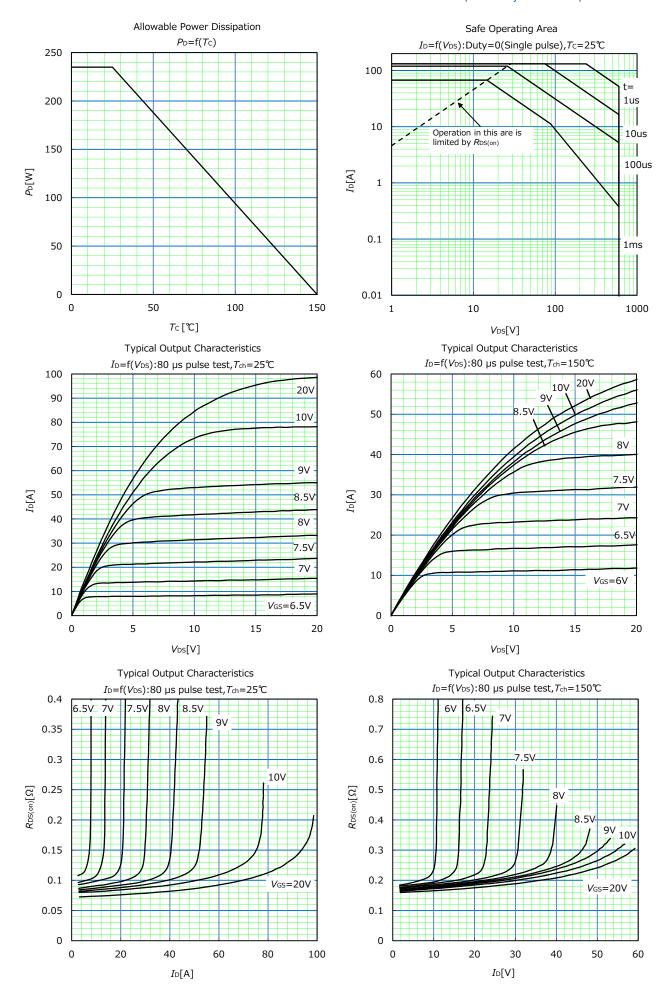
Note *7 : $C_{0(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V. Note *8 : $C_{0(er)}$ is a fixed capacitance that gives the same charging times as C_{oss} while V_{DS} is rising from 0 to 400V.

Reverse Diode

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode Forward On-Voltage	V _{SD}	I _{SD} =32.8A, V _{GS} =0V T _{ch} =25°C	-	0.95	1.35	V
Reverse Recovery Time	trr	- V₀₀=400V, /₅₀=32.8A -di/dt=100A/μs 7₅h=25°C See Fig.6 and Fig.7	-	370	-	ns
Reverse Recovery Charge	Qrr		-	6.5	-	μC
Peak Reverse Recovery Current	I rp		-	33	-	А

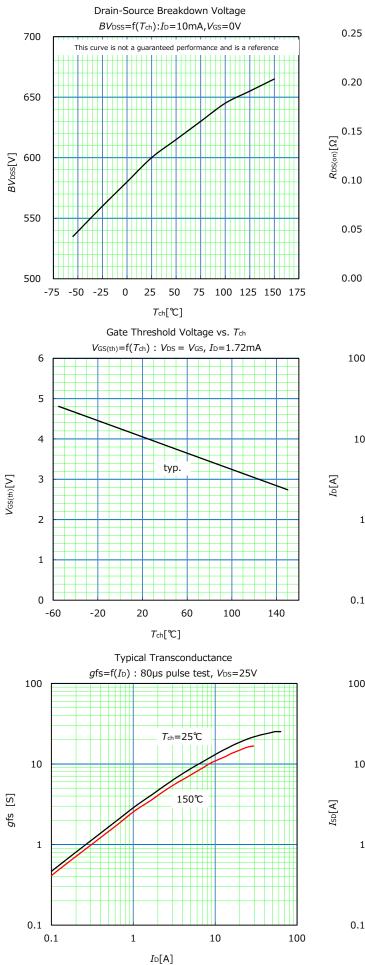
Thermal Resistance

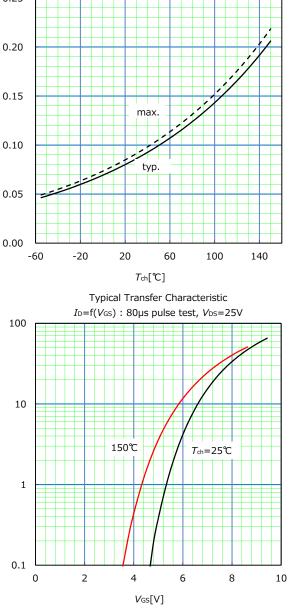
Parameter	Symbol	min.	typ.	max.	Unit
Channel to Case	Rth(ch-c)	-	-	0.53	°C/W
Channel to Ambient	R _{th(ch-a)}	-	-	62	°C/W



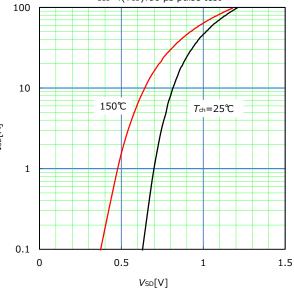
Drain-Source On-state Resistance

 $R_{DS(on)} = f(T_{ch}): I_D = 16.4 \text{A}, V_{GS} = 10 \text{V}$



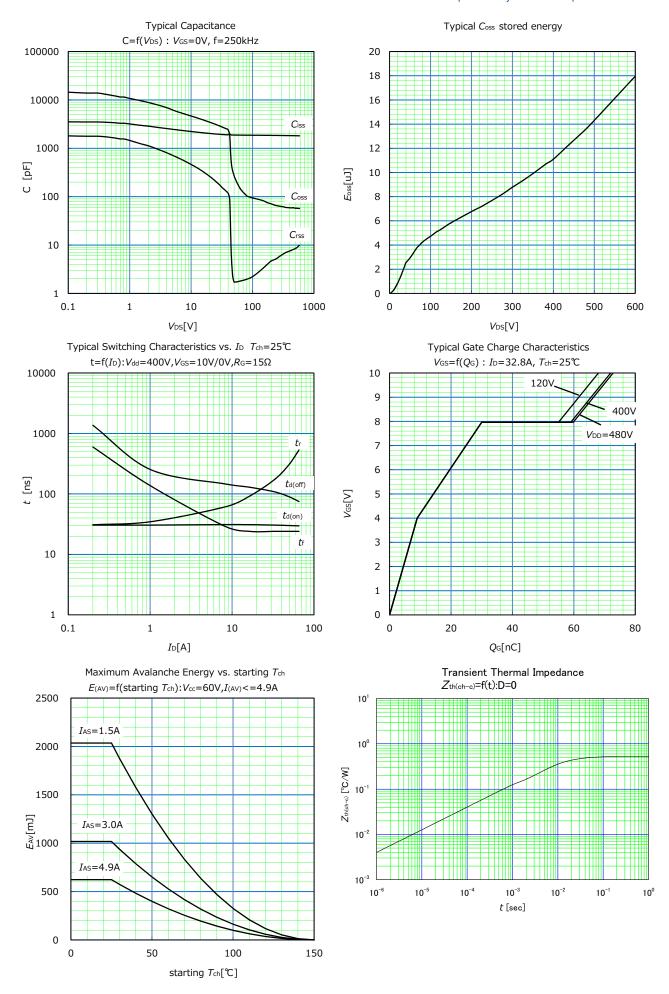


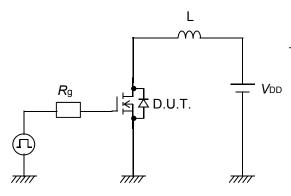
Typical Forward Characteristics of Reverse Diode $I_{SD}=f(V_{SD}):80 \ \mu s \ pulse \ test$

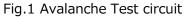


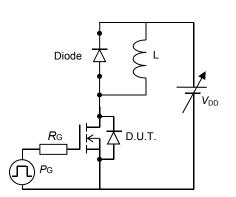
FMP60N088S2HF

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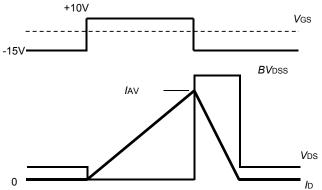


Fig.2 Operating waveforms of Avalanche Test

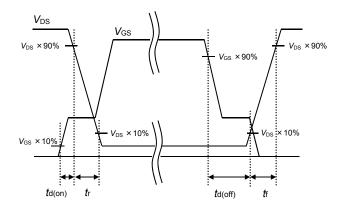


Fig.4 Operating waveform of Switching Test

Fig.3 Switching Test circuit



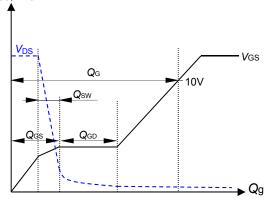
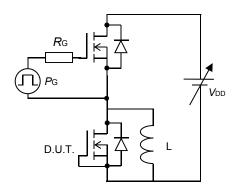


Fig.5 Operating waveform of Gate charge Test



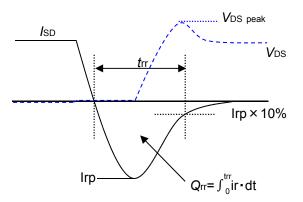
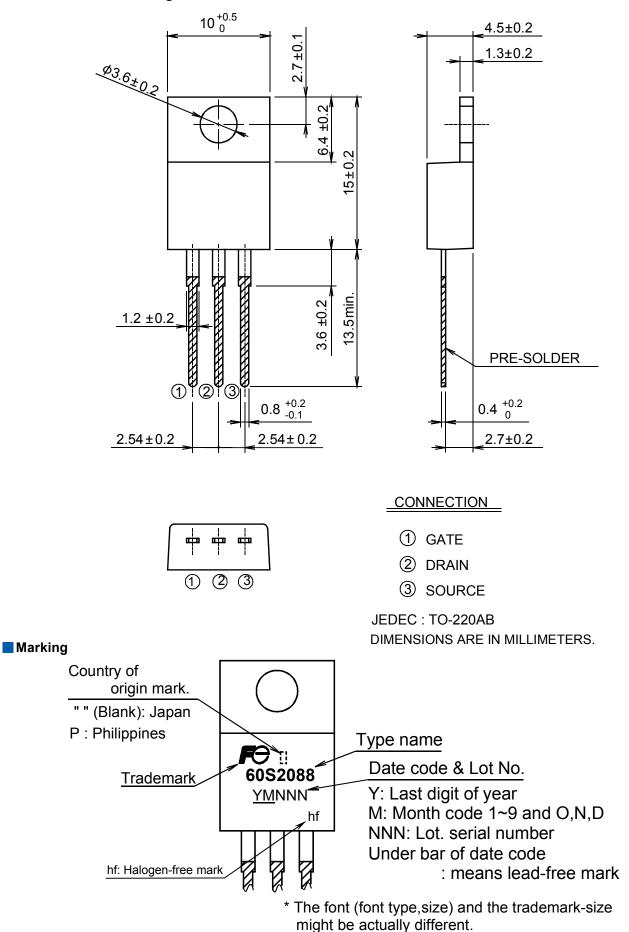


Fig.6 Reverse recovery Test circuit

Fig.7 Operating waveform of Reverse recovery Test

Outview: TO-220 Package



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